

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

NISHIMOTO et al

Serial No.: 08/897,839

Filed: July 21, 1997

For: STRESS-ADJUSTED INSULATING
FILM FORMING METHOD,
SEMICONDUCTOR DEVICE AND
METHOD OF MANUFACTURING THE
SAME

Group Art Unit: 2814

Examiner: K. Eaton



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Amdt. B
Cheresow
11-29-99

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Preliminary to examination of the Continuing Prosecution
Application (CPA) identified above, please amend the captioned
application as follows:

IN THE CLAIMS:

Please cancel claims 2-4, 6, 8-14, 16, 17 and 19-32 and add
the following new claims:

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B
--33. A stress-adjusted insulating film forming method for forming
a multilayered insulating film on a substrate, said method
comprising:

(a) forming a first insulating layer with a first type of
stress;